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ON5088 NPN wideband silicon germanium RF transistor

Rev. 3 — 12 December 2012

Product data sheet

1. Product profile

1.1 General description

NPN silicon germanium microwave transistor for high speed, low noise applications in a plastic, 4-pin dual-emitter SOT343F package.

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

1.2 Features and benefits

- Low noise high gain microwave transistor
- High maximum stable gain 27 dB at 1.8 GHz
- 110 GHz f_T silicon germanium technology

1.3 Applications

- 2nd and 3rd LNA stage in DBS LNBs
- Satellite radio
- Low noise amplifiers for microwave communications systems
- WLAN and WiMAX applications
- Analog/digital cordless applications

1.4 Quick reference data

Table 1. Quick reference data

	datok reference data					
Symbol	Parameter	Conditions	Mir	ι Тур	Max	Unit
V _{CB}	collector-base voltage	open emitter	-	-	10	V
V_{CE}	collector-emitter voltage	open base	-	-	3.0	V
		shorted base	-	-	10	V
V_{EB}	emitter-base voltage	open collector	-	-	1.0	V
I _C	collector current		-	25	40	mA
P _{tot}	total power dissipation	$T_{sp} \le 90 \ ^{\circ}C$	<u>[1]</u> -	-	136	mW
h _{FE}	DC current gain	$ I_C = 10 \text{ mA}; V_{CE} = 2 \text{ V}; $	160	280	400	
C _{CBS}	collector-base capacitance	$V_{CB} = 2 V$; f = 1 MHz	-	70	-	fF



NPN wideband silicon germanium RF transistor

Table 1.	QUICK reference data .	continued				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _T	transition frequency	$\label{eq:lc} \begin{array}{l} I_C = 25 \text{ mA}; \ V_{CE} = 2 \text{ V}; \\ f = 2 \text{ GHz}; \ T_{amb} = 25 \ ^\circ\text{C} \end{array}$	-	55	-	GHz
G _{p(max)}	maximum power gain	$\label{eq:lc} \begin{array}{l} I_C = 25 \text{ mA}; \ V_{CE} = 2 \text{ V}; \\ f = 12 \text{ GHz}; \ T_{amb} = 25 \ ^\circ\text{C} \end{array}$	[2] _	13	-	dB
NF	noise figure	$ I_C = 5 \text{ mA}; V_{CE} = 2 \text{ V}; $ f = 12 GHz; $\Gamma_S = \Gamma_{opt}; $ T _{amb} = 25 °C	-	1.1	-	dB

 Table 1.
 Quick reference data ...continued

[1] T_{sp} is the temperature at the solder point of the emitter lead.

[2] $G_{p(max)}$ is the maximum power gain, if K > 1. If K < 1 then $G_{p(max)}$ = Maximum Stable Gain (MSG).

2. Pinning information

Table 2.	Discrete pinning		
Pin	Description	Simplified outline	Graphic symbol
1	emitter		
2	base		4
3	emitter		2
4	collector		'`
			1, 3 <i>mbb159</i>

3. Ordering information

Table 3. Order	Table 3. Ordering information				
Type number Package					
	Name	Description	Version		
ON5088	-	plastic surface-mounted flat pack package; reverse pinning; 4 leads	SOT343F		

4. Marking

Table 4. Marking		
Type number	Marking	Description
ON5088	*6N	* = p : made in Hong Kong
	* = t : made in Malaysia	
		* = W : made in China

Product data sheet

NPN wideband silicon germanium RF transistor

Limiting values 5.

Table 5. In accordar	Limiting values nce with the Absolute Maximu	um Rating System ((IEC 60134).		
Symbol	Parameter	Conditions	Min	Max	Unit
V _{CB}	collector-base voltage	open emitter	-	10	V
V _{CE}	collector-emitter voltage	open base	-	3.0	V
		shorted base	-	10	V
V_{EB}	emitter-base voltage	open collector	-	1.0	V
I _C	collector current		-	40	mA
P _{tot}	total power dissipation	$T_{sp} \le 90 \ ^{\circ}C$	<u>[1]</u> -	136	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C

[1] T_{sp} is the temperature at the solder point of the emitter lead.

Thermal characteristics 6.

Table 6.	Thermal characteristics			
Symbol	Parameter	Conditions	Тур	Unit
R _{th(j-sp)}	thermal resistance from junction to solder point		440	K/W

Characteristics 7.

Tab	ole 7.	Characteristics
-	05 00	, ,, ,

Table 7. <i>T_j</i> = 25 ℃	Characteristics Cunless otherwise specified.					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{(BR)CBO}	collector-base breakdown voltage	$I_{C} = 2.5 \ \mu A; I_{E} = 0 \ mA$	10	-	-	V
V _{(BR)CEO}	collector-emitter breakdown voltage	$I_C = 1 \text{ mA}; I_B = 0 \text{ mA}$	3.0	-	-	V
I _C	collector current		-	25	40	mA
I _{CBO}	collector-base cut-off current	$I_E = 0 \text{ mA}; V_{CB} = 4.5 \text{ V}$	-	-	100	nA
h _{FE}	DC current gain	$I_{C} = 10 \text{ mA}; V_{CE} = 2 \text{ V}$	160	280	400	
C _{CES}	collector-emitter capacitance	V _{CB} = 2 V; f = 1 MHz	-	268	-	fF
C _{EBS}	emitter-base capacitance	V _{EB} = 0.5 V; f = 1 MHz	-	400	-	fF
C _{CBS}	collector-base capacitance	V _{CB} = 2 V; f = 1 MHz	-	70	-	fF
f _T	transition frequency	I_{C} = 25 mA; V_{CE} = 2 V; f = 2 GHz; T_{amb} = 25 °C	-	55	-	GHz
G _{p(max)}	maximum power gain	$I_{C} = 25 \text{ mA}; V_{CE} = 2 \text{ V}; T_{amb} = 25 \text{ °C}$	[1]			
		f = 1.8 GHz	-	27	-	dB
		f = 12 GHz	-	13	-	dB
$ s_{21} ^2$	insertion power gain	$I_{C} = 25 \text{ mA}; V_{CE} = 2 \text{ V}; T_{amb} = 25 \text{ °C}$				
		f = 1.8 GHz	-	25.4	-	dB
		f = 12 GHz	-	9.3	-	dB

NPN wideband silicon germanium RF transistor

Table 7.	Characteristics	continued
$T_i = 25 \ ^{\circ}C$	unless otherwise s	specified

T _j = 25 °C unless otherwise specified.						
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
NF	noise figure	$I_C = 5 \text{ mA}; V_{CE} = 2 \text{ V}; \Gamma_S = \Gamma_{opt}; T_{amb} = 25 \text{ °C}$				
		f = 1.8 GHz	-	0.43	-	dB
		f = 12 GHz	-	1.1	-	dB
G _{ass}	associated gain	$I_C = 5 \text{ mA}; V_{CE} = 2 \text{ V}; \Gamma_S = \Gamma_{opt}; T_{amb} = 25 \text{ °C}$				
		f = 1.8 GHz	-	22	-	dB
		f = 12 GHz	-	10	-	dB
P _{L(1dB)}	output power at 1 dB gain compression	I _C = 25 mA; V _{CE} = 2 V; Z _S = Z _L = 50 Ω; T _{amb} = 25 °C; f = 1.8 GHz	-	9	-	dBm
IP3	third-order intercept point	I_{C} = 25 mA; V _{CE} = 2 V; Z _S = Z _L = 50 Ω; T _{amb} = 25 °C; f ₂ = f ₁ + 1 MHz; f ₁ = 1.8 GHz	-	17	-	dBm

 $\label{eq:general} \mbox{[1]} \quad G_{p(max)} \mbox{ is the maximum power gain, if $K > 1$. If $K < 1$ then $G_{p(max)} = MSG$.}$

Product data sheet

ON5088 NPN wideband silicon germanium RF transistor

8. Package outline

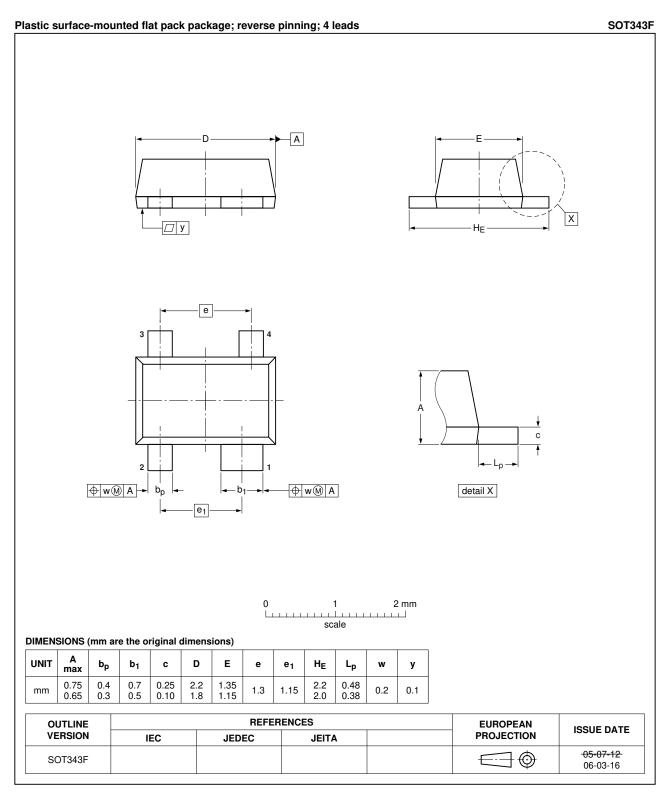


Fig 1. Package outline SOT343F

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NPN wideband silicon germanium RF transistor

9. Abbreviations

Table 8.	Abbreviations
Acronym	Description
DBS	Direct Broadcast Satellite
DC	Direct Current
DRO	Dielectric Resonator Oscillator
LNA	Low Noise Amplifier
LNB	Low Noise Block
NPN	Negative-Positive-Negative
RF	Radio Frequency
WLAN	Wireless Local Area Network
WiMAX	Worldwide Interoperability for Microwave Access

10. Revision history

Table 9. Revision I	nistory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
ON5088 v.3	20121212	Product data sheet	-	ON5088 v.2
Modifications:		b <mark>age 1</mark> : some changes hav bage 3: some changes hav		
		bage 3: The minimum value		changed.
ON5088 v.2	20111222	Product data sheet	-	ON5088 v.1
ON5088 v.1	20100422	Product data sheet	-	-

11. Legal information

11.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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NPN wideband silicon germanium RF transistor

13. Contents

1	Product profile 1
1.1	General description 1
1.2	Features and benefits 1
1.3	Applications 1
1.4	Quick reference data 1
2	Pinning information 2
3	Ordering information 2
4	Marking
5	Limiting values 3
6	Thermal characteristics 3
7	Characteristics 3
8	Package outline 5
9	Abbreviations 6
10	Revision history 6
11	Legal information 7
11.1	Data sheet status 7
11.2	Definitions7
11.3	Disclaimers 7
11.4	Trademarks8
12	Contact information 8
13	Contents

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